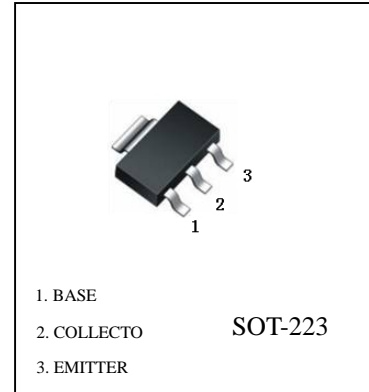


BSP52 (NPN)

FEATURES

- This device is designed for applications requiring extremely high current gain at collector currents to 500mA.
- Sourced from process 03.



Absolute Maximum Ratings* $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	80	V
V_{CBO}	Collector-Base Voltage	90	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current - Continuous	800	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	- 55 ~ +150	$^\circ\text{C}$

Thermal Characteristics $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max.	Units
P_D	Total Device Dissipation Derate above 25°C	1000 8.0	mW mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	$^\circ\text{C}/\text{W}$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C .
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\mu\text{A}, I_E = 0$	90			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}, I_C = 0$	5			V
I_{CES}	Collector Cutoff Current	$V_{CE} = 80\text{V}, V_{BE} = 0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0\text{V}, I_C = 0$			10	μA
On Characteristics						
h_{FE}	DC Current Gain	$I_C = 150\text{mA}, V_{CE} = 10\text{V}$ $I_C = 500\text{mA}, V_{CE} = 10\text{V}$	1000 2000			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 500\text{mA}, I_B = 0.5\text{mA}$			1.3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 500\text{mA}, I_B = 0.5\text{mA}$			1.9	V